

Super-Junction Power Mosfet

1. Product Information

Features

- Low FOM $R_{DS(ON)} \times Q_G$
- Better EMI
- Extremely low switching loss
- Good stability and uniformity
- 100% UIS and Isolation Tested

Pin Description

Pin	Description
1	Gate(G)
2	Drain(D)
3	Source(S)

Applications

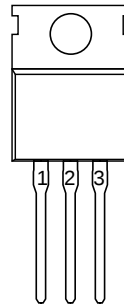
- Swit Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- Charge

Quick reference

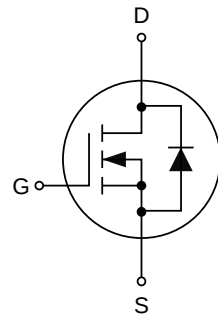
- $V_{DS} \geq 650\text{ V}$
- $I_D \leq 20\text{ A}$
- $R_{DS(ON)} \leq 190\text{ m}\Omega @ V_{GS} = 10\text{ V}$ (Type 160 mΩ)

Simplified Outline

Symbol



Top View
TO-220



Package Marking and Ordering Information

Product Name	Marking	Package	Packaging	Quantity (pcs)
KJC65R190C	KJC65R190C	TO-220	Tube	50

2. Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Values	Unit
V_{DS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Continuous Drain Current ($T_C=25^\circ\text{C}$)	20	A
	Continuous Drain Current ($T_C=100^\circ\text{C}$)	12.5	A
I_{DM}	Pulsed Drain Current ^[1]	80	A
E_{AS}	Single Pulsed Avalanche Energy ^[2]	388	mJ
P_D	Power Dissipation ^[2]	223	W
dv/dt	Peak Diode Recovery dv/dt	5	V/ns
T_J, T_{stg}	Operating Junction and Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction-Ambient ^[3]	74	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-Case ^[3]	0.56	$^\circ\text{C/W}$

3. Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Type	Max	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0 V, I _D =250 μA	650	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =650 V, V _{GS} =0 V,	-	-	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±30 V, V _{DS} =0 V	-	-	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250 μA	2.5	3.5	4.5	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10 V, I _D =20 A	-	160	190	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =100 V, V _{GS} =0 V, f=1 MHz	-	1655	-	pF
C _{oss}	Output Capacitance		-	69	-	pF
C _{rss}	Reverse Transfer Capacitance		-	1.2	-	pF
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =325 V, I _D =20 A, R _G =25 Ω, V _{GS} =10V	-	34	-	ns
t _r	Turn-on Rise Time		-	37	-	ns
t _{d(off)}	Turn-off Delay Time		-	148	-	ns
t _f	Turn-off Fall Time		-	36	-	ns
Q _g	Total Gate Charge	V _{DS} =325 V, I _D =20 A, V _{GS} =10 V	-	34	-	nC
Q _{gs}	Gate-Source Charge		-	7	-	nC
Q _{gd}	Gate-Drain Charge		-	12	-	nC
Source-Drain Diode Characteristics						
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} =0V, I _F =20 A	-	-	1.4	V
I _S	Diode Continuous Forward Current		-	-	20	A
I _{SM}	Maximum Pulsed Body-Diode Forward Current		-	-	60	A
Q _{rr}	Reverse Recovery Time	V _R =50 V, I _F =20 A, di/dt=100 A/μs	-	4.47	-	μC
T _{rr}	Reverse Recovery Charge		-	301	-	ns

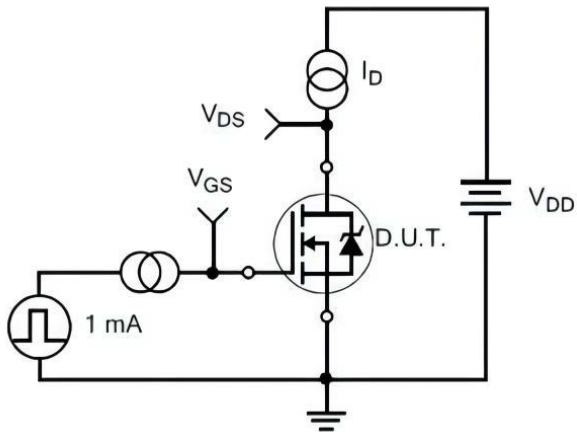
Notes:

1. Limited by maximum junction temperature, maximum duty cycle is 0.75.
2. T_J=25°C, V_{DD}=50 V, V_{GS}=10 V, R_G=25 Ω.
3. Mount on minimum PCB layout.

4. Test Circuits and Waveforms ($T_J=25^\circ\text{C}$, unless otherwise noted)

Table 1. Gate Charge Test Circuit and Waveforms

Gate Charge Test Circuit



Gate Charge Waveforms

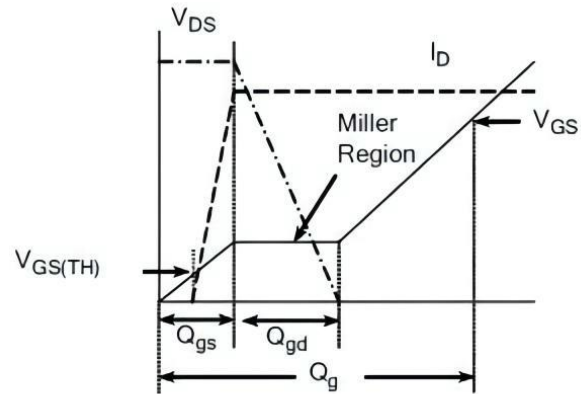
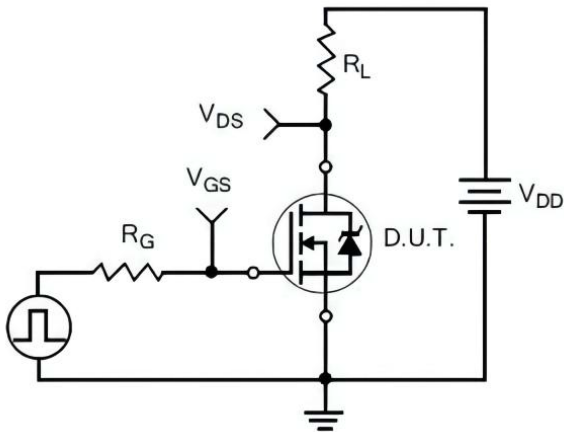


Table 2. Resistive Switching Test Circuit and Waveforms

Resistive Switching Test Circuit



Resistive Switching Waveforms

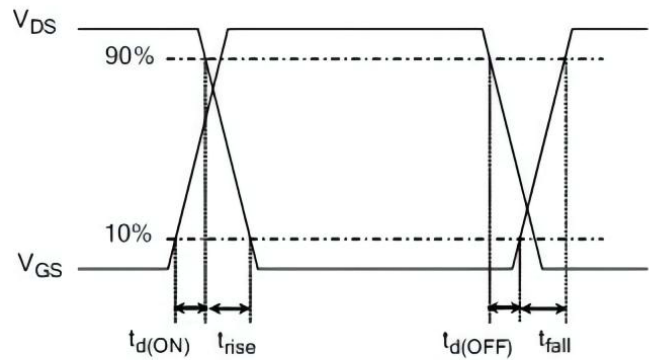
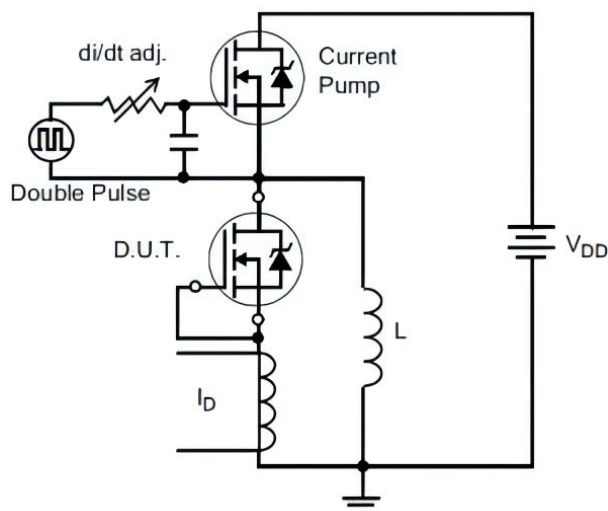


Table 3. Diode Recovery Test Circuit and Waveforms

Diode Recovery Test Circuit



Diode Recovery Waveforms

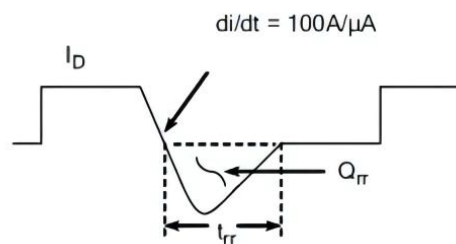
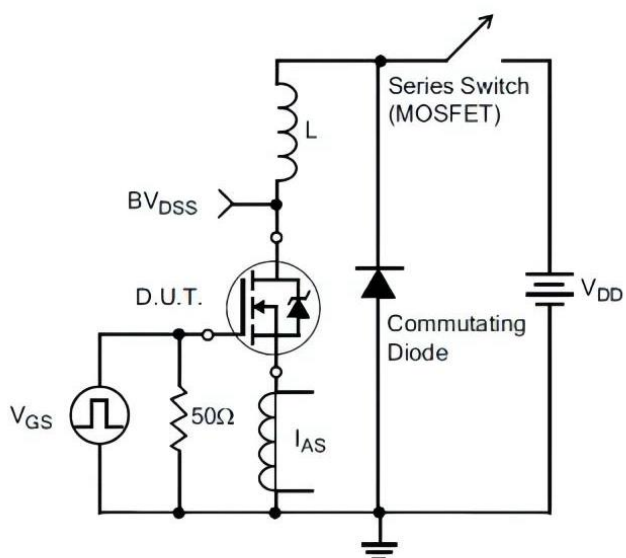
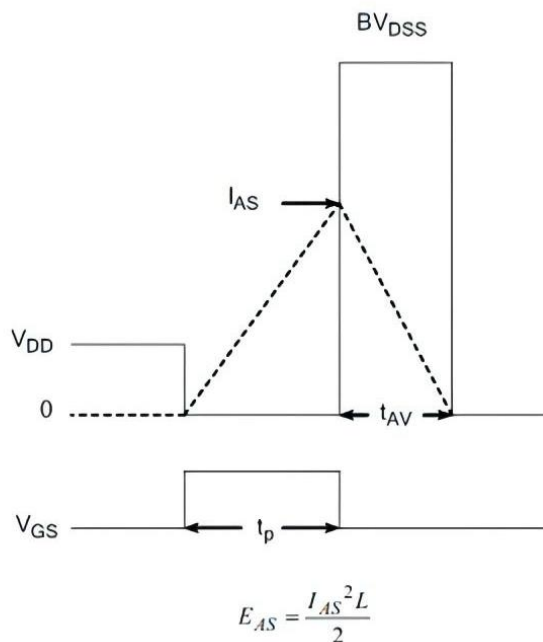


Table 4. Unclamped inductive Switching (UIS) Test Circuit and Waveforms

Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms



5. Electrical Characteristics

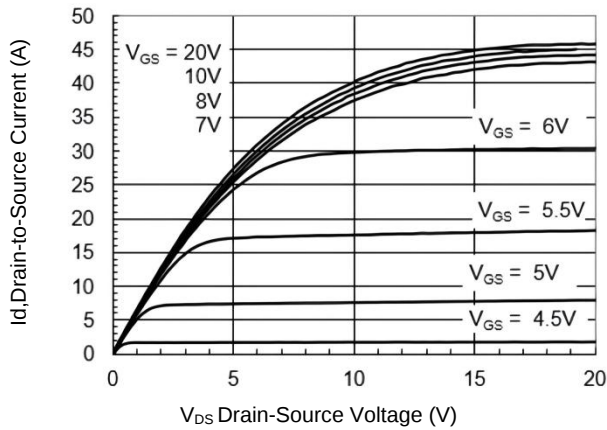


Figure 1. Typical Output Characteristics

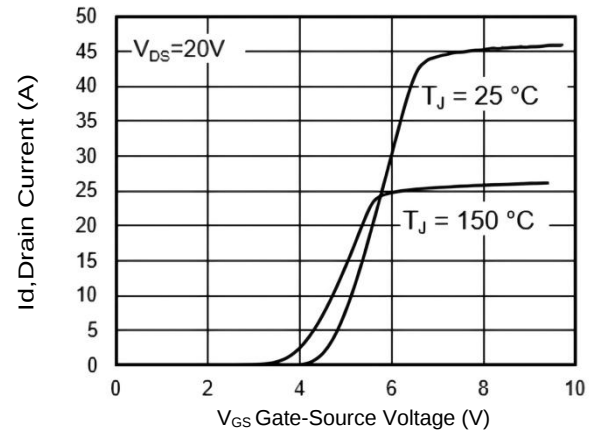


Figure 2. Typical Transfer Characteristics

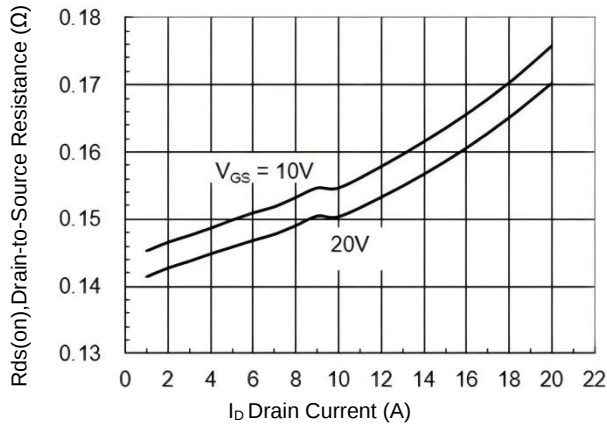


Figure 3. On-Resistance versus Drain Current

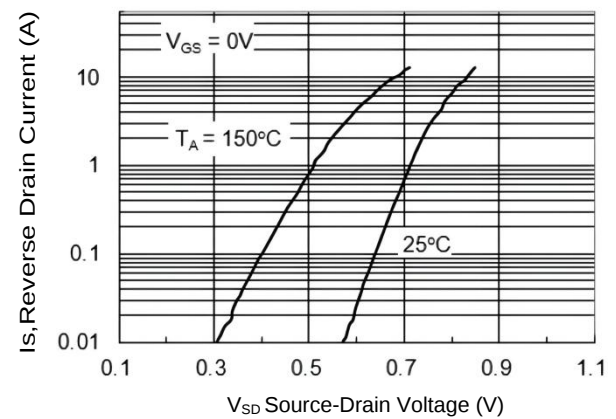


Figure 4. Diode forward voltage versus Current

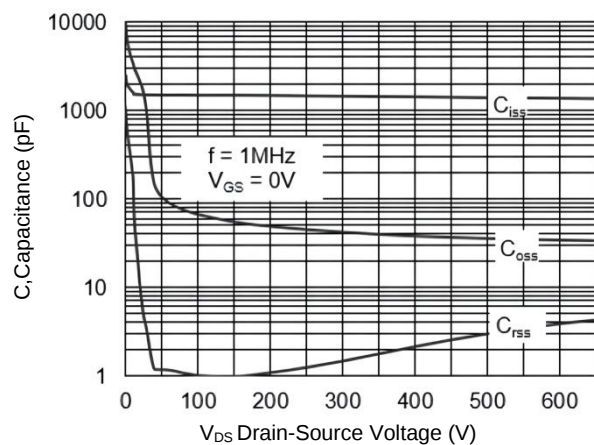


Figure 5. Typical Capacitance versus V_{DS}

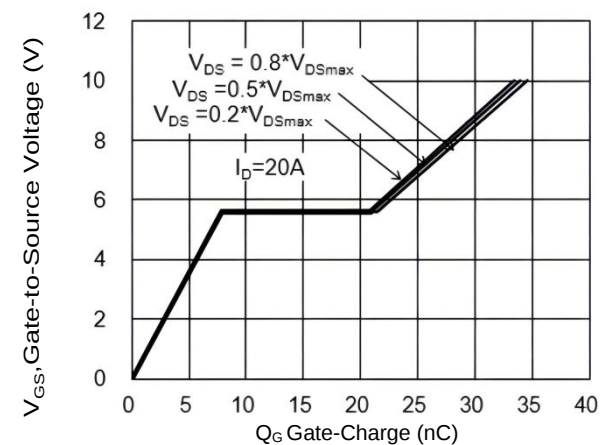


Figure 6. Typical Gate Charge versus V_{GS}

5. Electrical Characteristics (cont.)

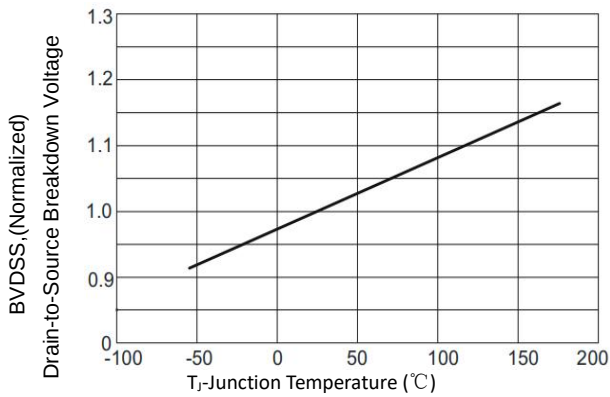


Figure 7. BV_{DSS} Variation with Temperature

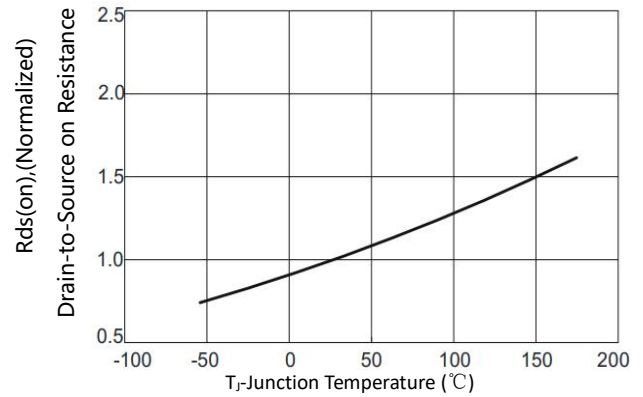


Figure 8. On-Resistance Variation with Temperature

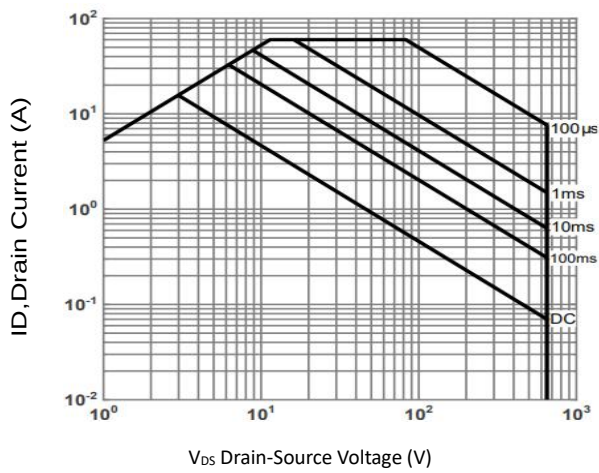


Figure 9. Maximum Safe Operating Area

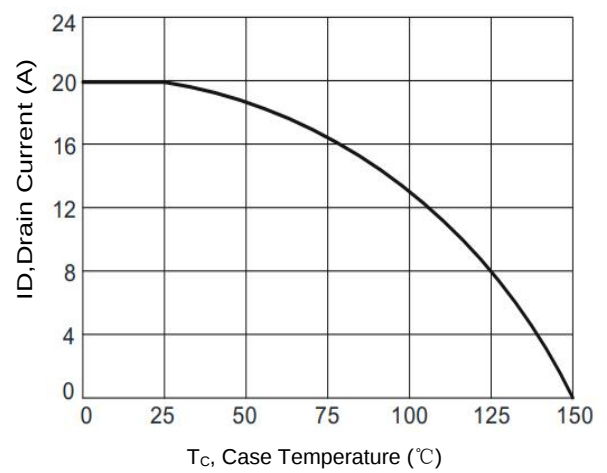
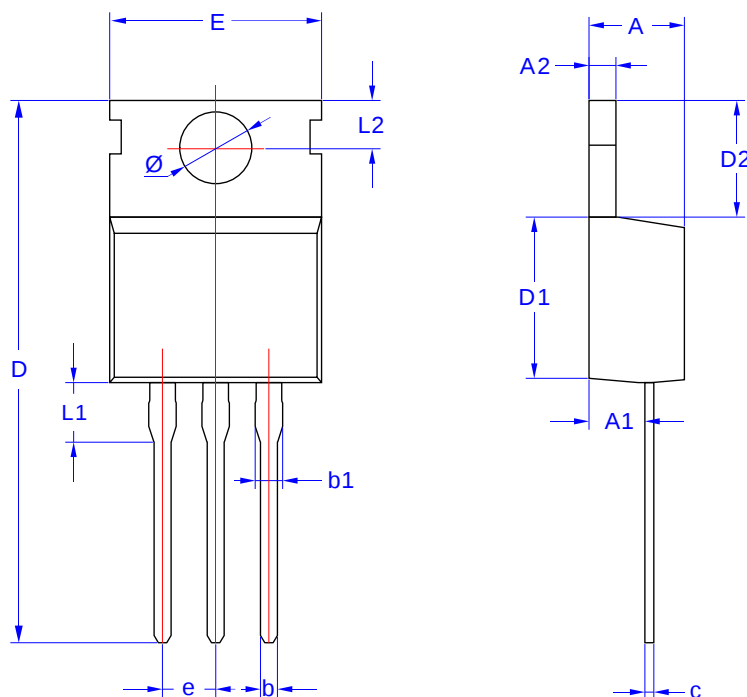


Figure 10. Maximum Continuous Drain Current versus Case Temperature

6. Package Mechanical Data

● TO-220 Package



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	4.24	4.70
A1	2.20	3.00
A2	1.15	1.40
b	0.70	0.95
b1	1.14	1.70
c	0.40	0.60
D	28.0	29.8
D1	8.80	9.90
D2	6.25	6.90
E	9.70	10.50
L1	3.80	
L2	2.40	3.00
e	2.54 BSC	
Φ	3.60	